

	Type	Hits	Search Text	DBs	Time Stamp
1	IS&R	1305	(438/649,585).CCLS.	USPAT	2006/10/01 23:50
2	BRS	1336	S8 and (insulat\$3 dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/10/01 23:59
3	BRS	1850	S5 and ((w tungsten) (zr zirconium) (hf hafnium) (v vanadium) (nb niobium) (ti titanium) (cr chromium)) and ((wn tungsten adj nitride) (zrn zirconium adj nitride) (hfn hafnium adj nitride) (vn vanadium adj nitride) (nbn niobium adj nitride) (tin titanium adj nitride) (crn chromium adj nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/10/01 23:57
4	IS&R	1450	(257/369,402,407).CCLS.	USPAT	2006/10/01 23:48
5	BRS	1210	S10 and different	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/10/01 23:59
6	BRS	68843	semiconductor and (cmos or complementary)	USPAT	2006/10/01 23:50
7	BRS	130259	semiconductor and (cmos or complementary)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/10/01 23:50

	Type	Hits	Search Text	DBs	Time Stamp
8	BRS	1344	S7 and (gate adj electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/10/01 23:57
9	BRS	3776	S4 and ((work adj function) (fermi adj level))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/10/01 23:51